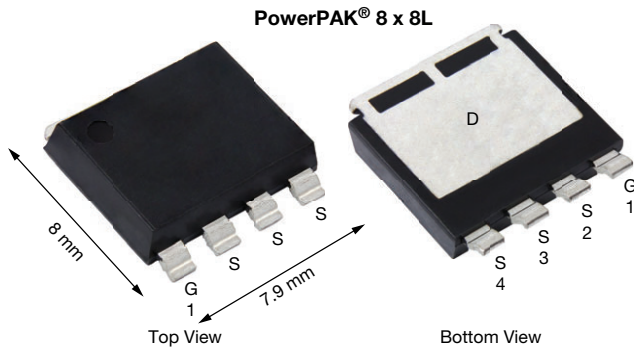


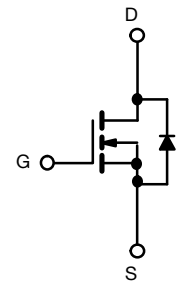
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_G and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



N-Channel MOSFET

PRODUCT SUMMARY

V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00124
I _D (A)	460
Configuration	Single
Package	PowerPAK 8 x 8L

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	40	V
Gate-source voltage	V _{GS}	± 20	
Continuous drain current	I _D	T _C = 25 °C	460
		T _C = 125 °C	265
Continuous source current (diode conduction)	I _S	450	A
Pulsed drain current ^b	I _{DM}	900	
Single pulse avalanche current	I _{AS}	48	mJ
Single pulse avalanche energy	E _{AS}	115.2	
Maximum power dissipation	P _D	T _C = 25 °C	500
		T _C = 125 °C	166
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^d		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R _{thJA}	44	°C/W
Junction-to-case (drain)	R _{thJC}	0.3	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



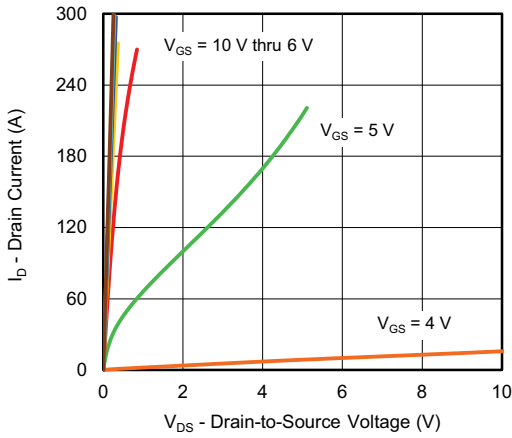
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	3	3.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	200	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	330	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	100	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	-	0.00100	0.00124	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.00200	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.00240	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 60\text{ A}$		-	150	-	S
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	5360	6975	pF
Output capacitance	C_{oss}			-	2070	2700	
Reverse transfer capacitance	C_{rss}			-	167	215	
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$	-	92	130	nC
Gate-source charge ^c	Q_{gs}			-	26	-	
Gate-drain charge ^c	Q_{gd}			-	20.1	-	
Gate resistance	R_g	f = 1 MHz		0.65	1.59	2.56	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	18.5	26	ns
Rise time ^c	t_r			-	18	25	
Turn-off delay time ^c	$t_{d(off)}$			-	37	52	
Fall time ^c	t_f			-	14	20	
Source-Drain Diode Ratings and Characteristics ^b							
Reverse recovery time	t_{rr}	$V_{DD} = 32\text{ V}, I_{FM} = 15\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}$		-	59	-	ns
Reverse recovery charge	Q_{rr}			-	69	-	nC
Reverse recovery current	I_{RM}			-	2	3.2	A
Pulsed current ^a	I_{SM}			-	-	900	A
Forward voltage	V_{SD}	$I_F = 50\text{ A}, V_{GS} = 0$		-	0.8	1.1	V

Notes

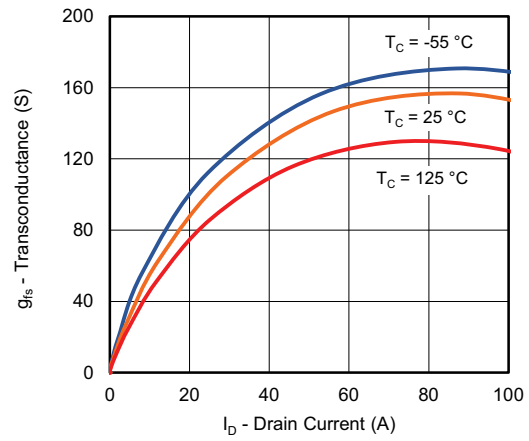
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\text{ }\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

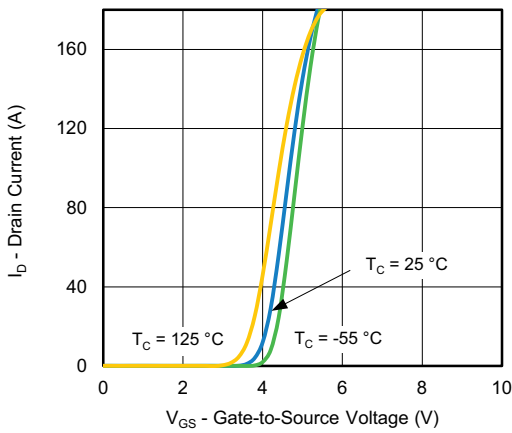
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



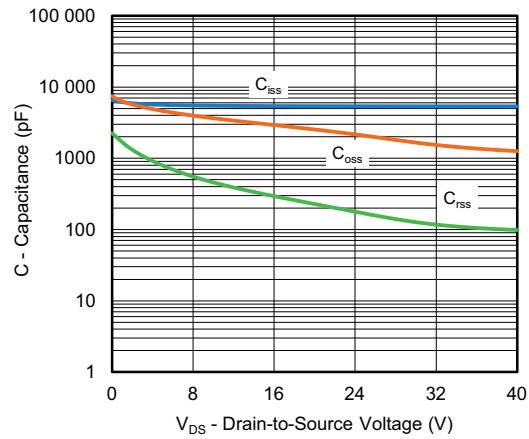
Output Characteristics



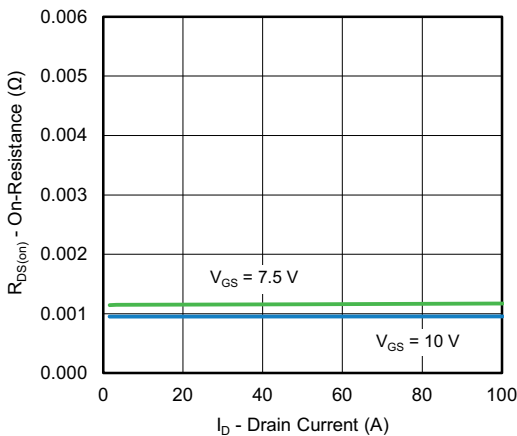
Transconductance



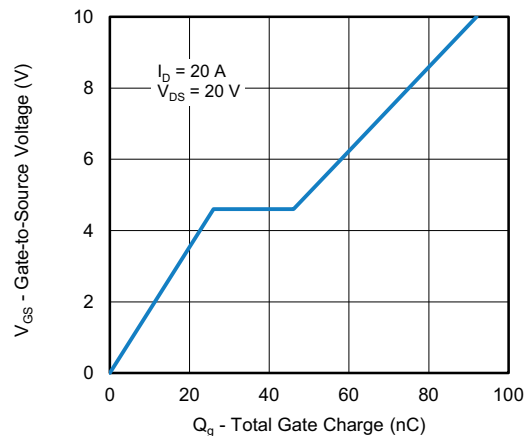
Transfer Characteristics



Capacitance

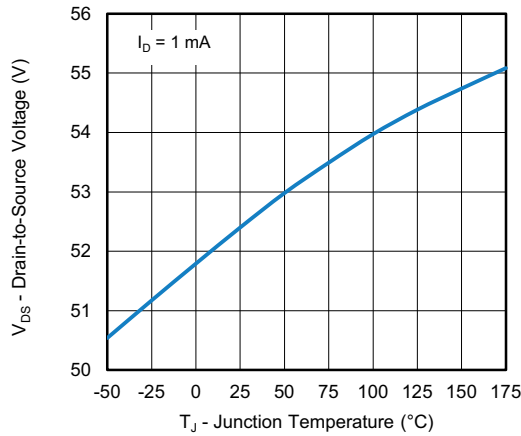


On-Resistance vs. Drain Current

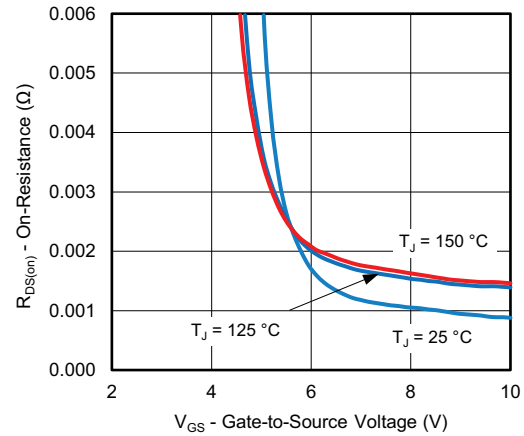


Gate Charge

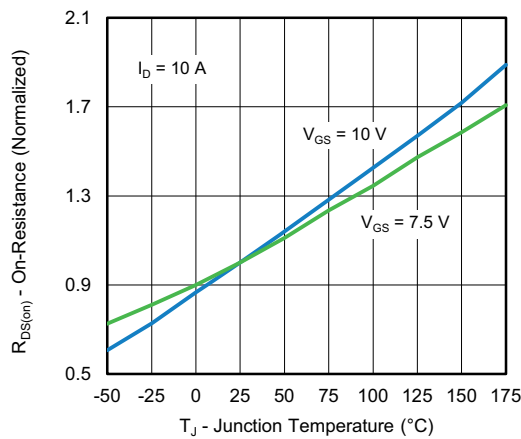
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



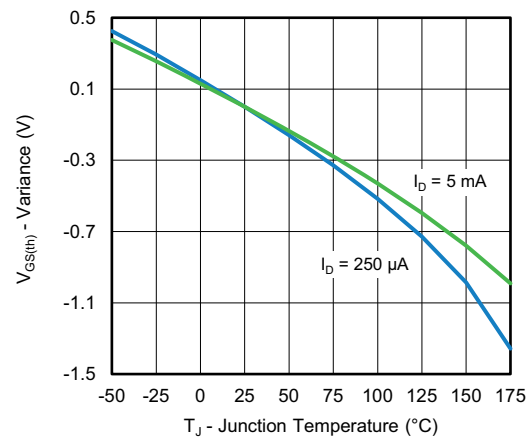
Drain Source Breakdown vs. Junction Temperature



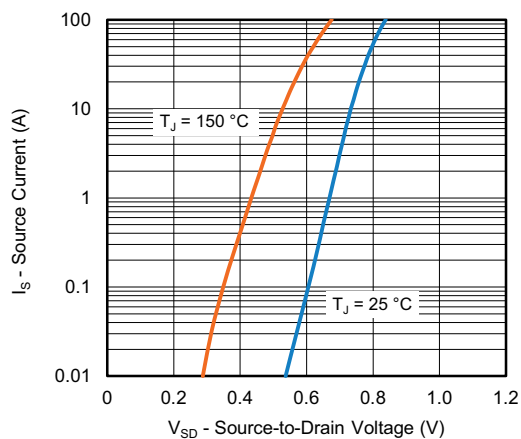
On-Resistance vs. Gate-to-Source Voltage



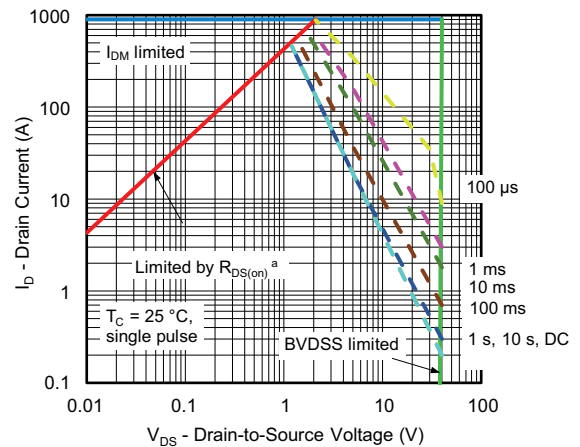
On-Resistance vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage



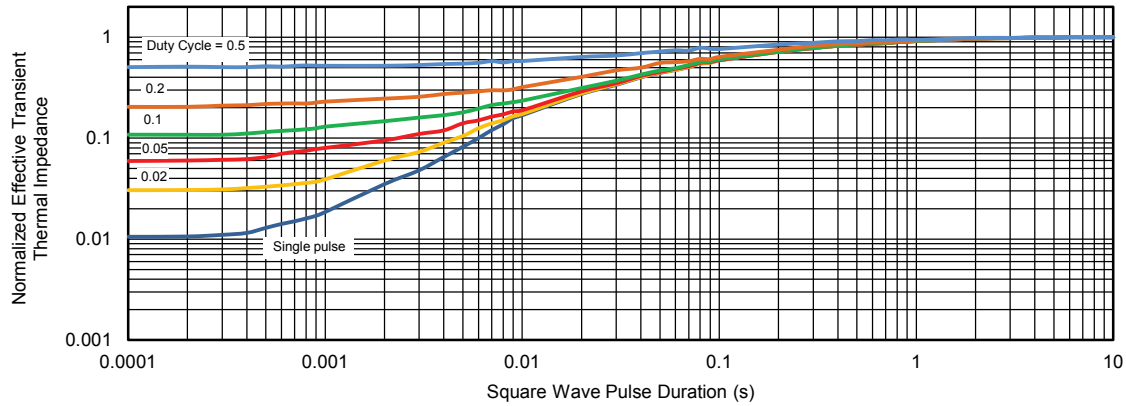
Safe Operating Area

Note

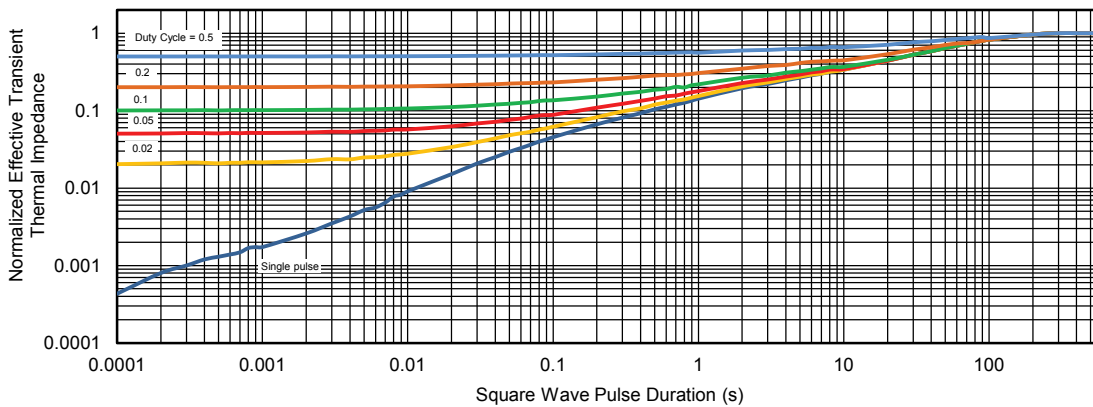
- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

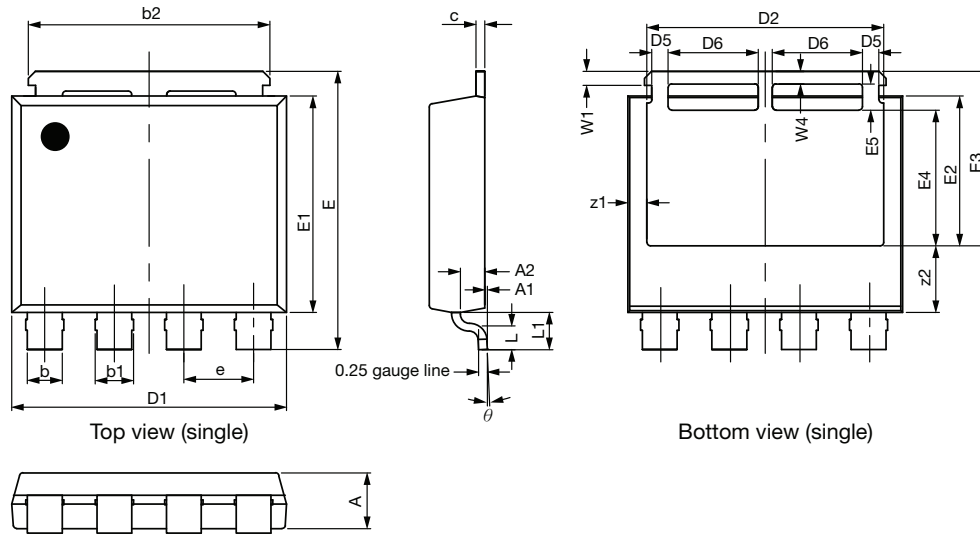


Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 8 x 8L BWL Case Outline 2



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
e	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°

ECN: S19-0643-Rev. B, 05-Aug-2019
DWG: 6073

Note

- Millimeter will govern



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